# LNA4801L

### GaAlAs Infrared Light Emitting Diode

#### For optical control systems

#### Features

- Fast response and high-speed modulation capability:  $f_c = 20$  MHz (typ.)
- Wide directivity:  $\theta = 22^{\circ}$  (typ.)
- Transparent epoxy resin package

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

| Parameter                     | Symbol           | Rating      | Unit |  |
|-------------------------------|------------------|-------------|------|--|
| Power dissipation             | P <sub>D</sub>   | 190         | mW   |  |
| Forward current               | I <sub>F</sub>   | 100         | mA   |  |
| Pulse forward current *       | I <sub>FP</sub>  | 1           | А    |  |
| Reverse voltage               | V <sub>R</sub>   | 3           | V    |  |
| Operating ambient temperature | T <sub>opr</sub> | -25 to +85  | °C   |  |
| Storage temperature           | T <sub>stg</sub> | -30 to +100 | °C   |  |

Note) \*: f = 100 Hz, Duty cycle = 0.1%

#### Electrical-Optical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter                  | Symbol            | Conditions                                  | Min   | Тур | Max | Unit  |
|----------------------------|-------------------|---|-------|-----|-----|-------|
| Reverse current            | I <sub>R</sub>    | $V_R = 3 V$                                 | Č     | 10% | 10  | μΑ    |
| Forward voltage            | V <sub>F</sub>    | I <sub>F</sub> = 100 mA                     | 8     | 1.6 | 1.9 | V     |
| Center radiant intensity   | Ie                | I <sub>F</sub> = 50 mA                      | 12    |     | 48  | mW/sr |
| Peak emission wavelength * | $\lambda_{\rm P}$ | $I_F = 50 \text{ mA}$                       | Dr. C | 860 |     | nm    |
| Spectral half band width * | Δλ                | $I_F = 50 \text{ mA}$                       | allo. | 40  |     | nm    |
| Half-power angle           | θ                 | The angle when the radiant power is halved. | 80    | 22  |     | 0     |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 measuring methods for diodes.

2. Cutoff frequency: 20 MHz

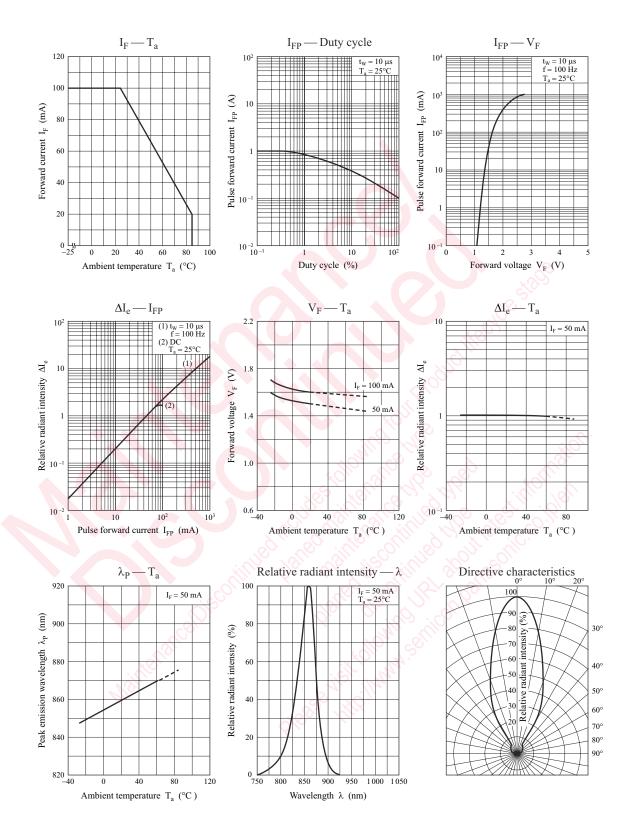
$$f_{\rm C}$$
: 10 × log  $\frac{P_{\rm O} \text{ at } f = f_{\rm C}}{P_{\rm O} \text{ at } f = 1 \text{ MHz}}$ 

3. \*: LED might radiate red light under large current drive.

= -3

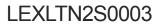
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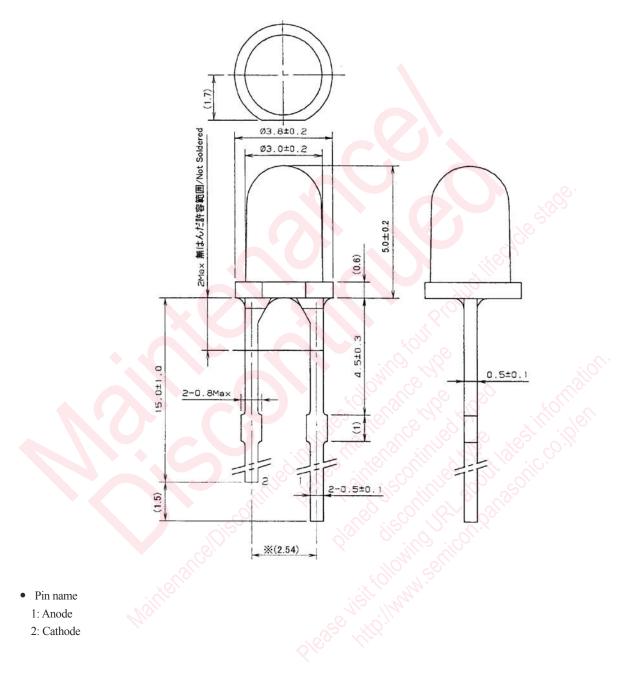
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Package (Unit: mm)





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